

### General Description

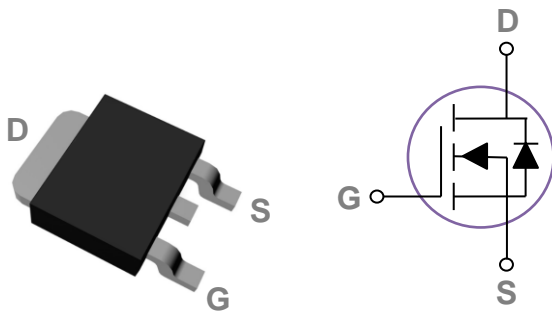
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
40V	2.8mΩ	130A

### Features

- 40V, 130A,  $R_{DS(ON)} = 2.8m\Omega @ V_{GS} = 10V$
- Improved  $dv/dt$  capability
- Fast switching
- Green Device Available

### TO252 Pin Configuration



### Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2<sup>nd</sup> SR

### Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ\text{C}$ )	130	A
	Drain Current – Continuous ( $T_c=100^\circ\text{C}$ )	83	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	520	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	312	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	79	A
$P_D$	Power Dissipation ( $T_c=25^\circ\text{C}$ )	101	W
	Power Dissipation – Derate above $25^\circ\text{C}$	0.81	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.23	$^\circ\text{C}/\text{W}$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	40	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.03	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
		V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	μA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>3</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =25A	---	2.3	2.8	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =12A	---	2.8	3.7	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	1.2	1.6	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5	---	mV/°C
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =2A	---	16	---	S

**Dynamic Characteristics**

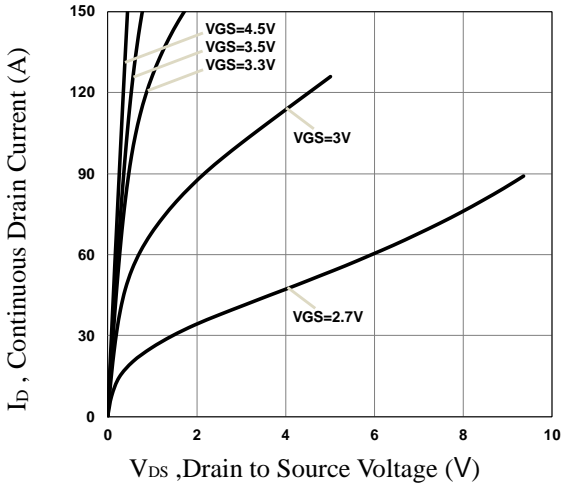
Q <sub>g</sub>	Total Gate Charge <sup>3,4</sup>	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =65A	---	96	180	nC
			---	44.4	80	
			---	9.6	18	
Q <sub>gs</sub>	Gate-Source Charge <sup>3,4</sup>	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =65A	---	9.6	18	nC
Q <sub>gd</sub>	Gate-Drain Charge <sup>3,4</sup>		---	16	30	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3,4</sup>		---	28	50	
T <sub>r</sub>	Rise Time <sup>3,4</sup>	V <sub>DD</sub> =20V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω I <sub>D</sub> =65A	---	3.2	6.5	ns
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3,4</sup>		---	89	160	
T <sub>f</sub>	Fall Time <sup>3,4</sup>		---	14	28	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, F=1MHz	---	5200	10000	pF
C <sub>oss</sub>	Output Capacitance		---	530	1000	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	430	800	
R <sub>g</sub>	Gate resistance		V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	1.4	

**Drain-Source Diode Characteristics**

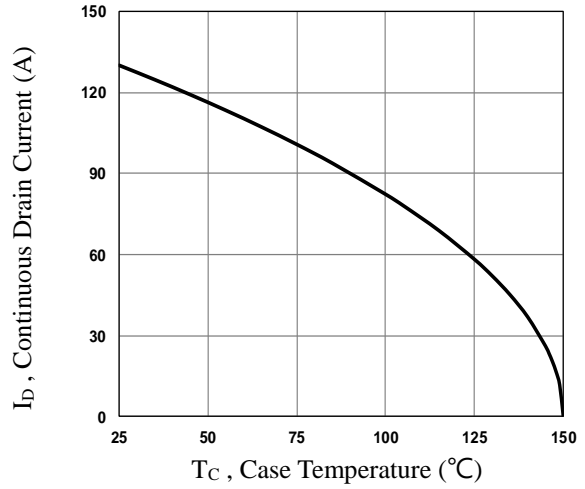
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	130	A
I <sub>SM</sub>	Pulsed Source Current <sup>3</sup>		---	---	260	A
V <sub>SD</sub>	Diode Forward Voltage <sup>3</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>R</sub> =30V, I <sub>S</sub> =10A	---	60	---	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/μs, T <sub>J</sub> =25°C	---	70	---	nC

Note :

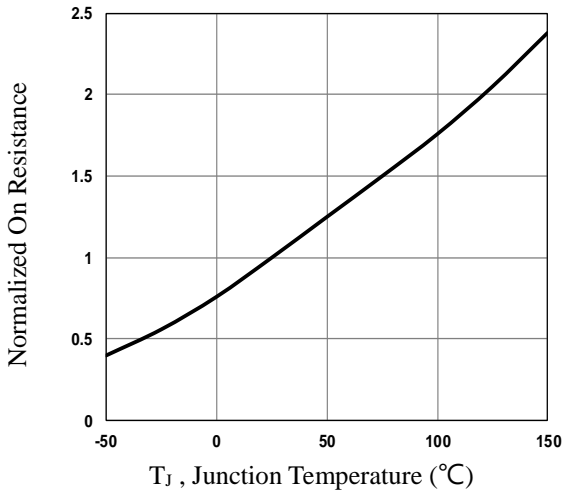
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=79A., Starting T<sub>J</sub>=25°C
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



**Fig.1 Typical Output Characteristics**



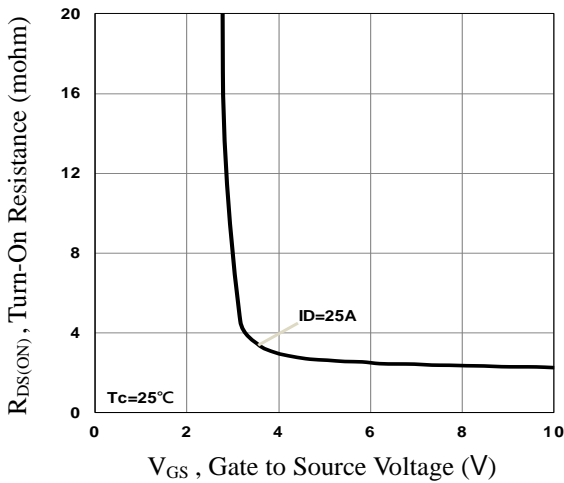
**Fig.2 Continuous Drain Current vs. T<sub>c</sub>**



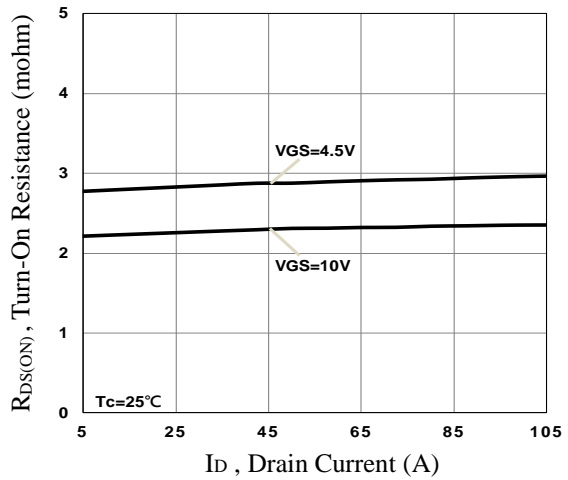
**Fig.3 Normalized R<sub>DS(on)</sub> vs. T<sub>j</sub>**



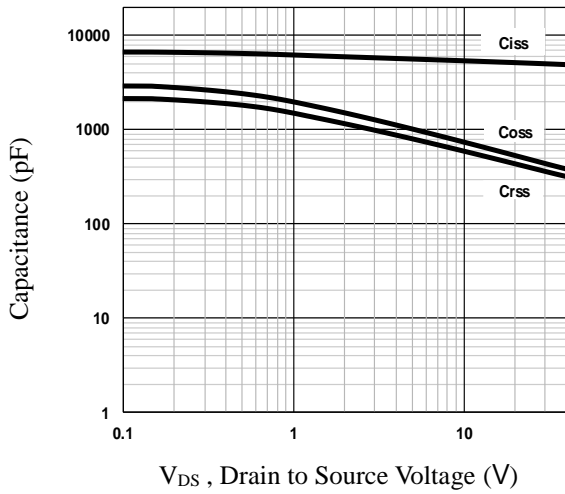
**Fig.4 Normalized V<sub>th</sub> vs. T<sub>j</sub>**



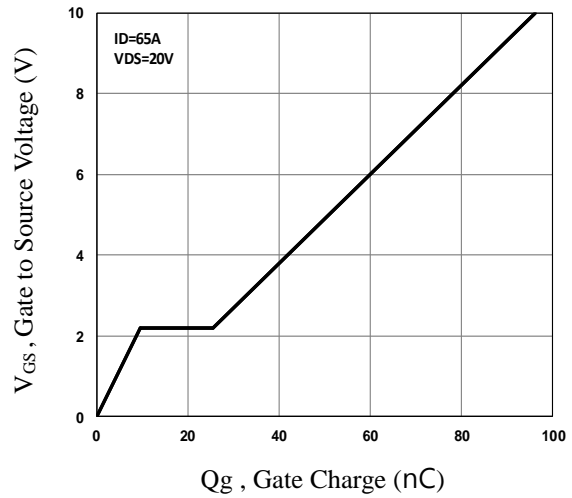
**Fig.5 Turn-On Resistance vs. V<sub>GS</sub>**



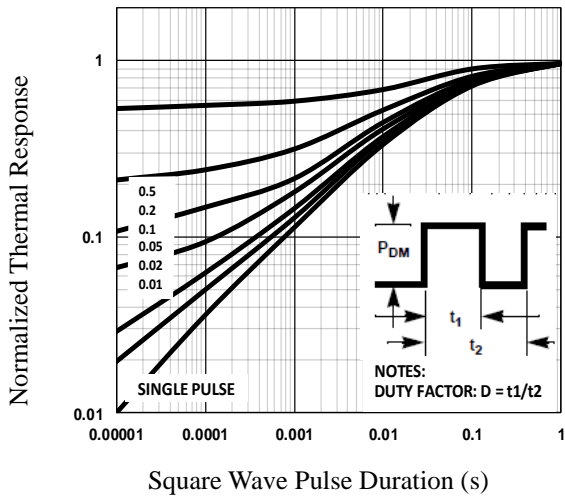
**Fig.6 Turn-On Resistance vs. I<sub>D</sub>**



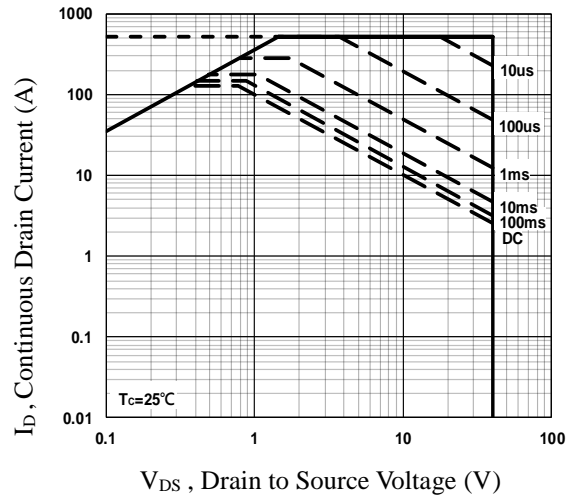
**Fig.7 Capacitance Characteristics**



**Fig.8 Gate Charge Characteristics**



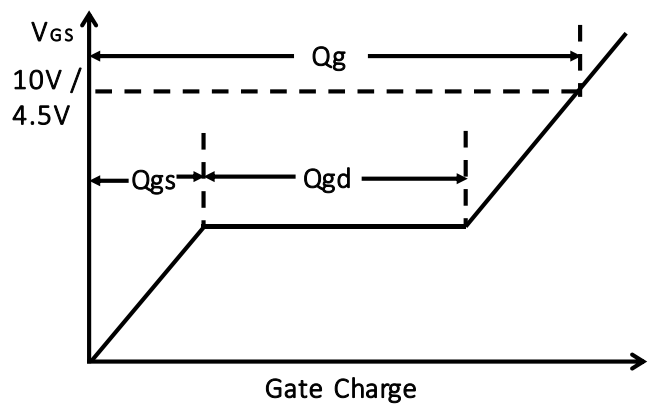
**Fig.9 Normalized Transient Impedance**



**Fig.10 Maximum Safe Operation Area**

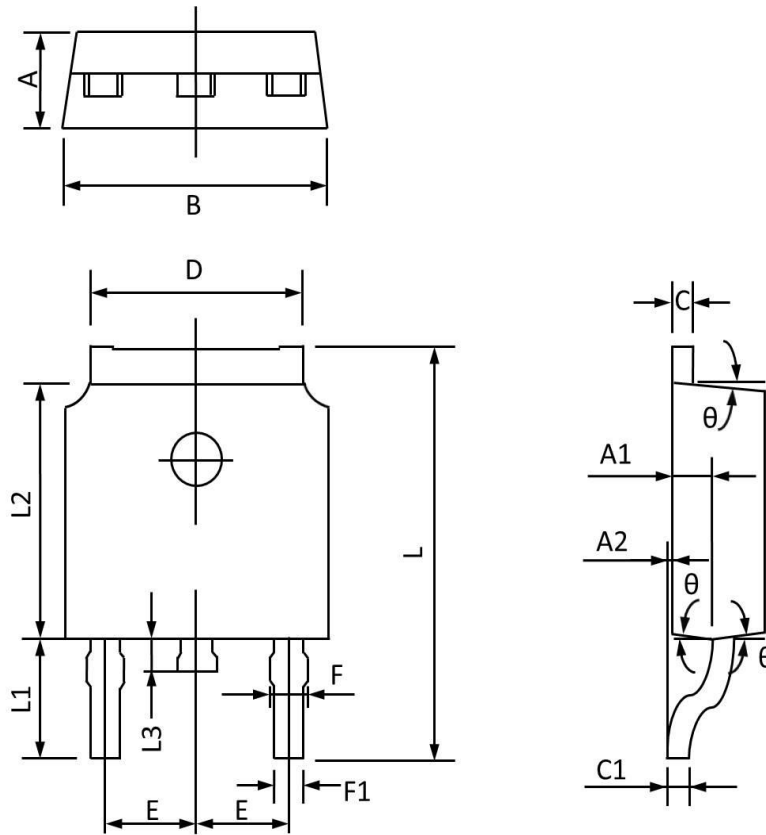


**Fig.11 Switching Time Waveform**



**Fig.12 Gate Charge Waveform**

## TO252 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	2.450	2.150	0.096	0.085
A1	1.200	0.910	0.047	0.036
A2	0.150	0.000	0.006	0.000
B	6.800	6.300	0.268	0.248
C	0.580	0.350	0.023	0.014
C1	0.550	0.380	0.022	0.015
D	5.500	5.100	0.217	0.201
E	2.390	2.000	0.094	0.079
F	0.940	0.600	0.037	0.024
F1	0.860	0.500	0.034	0.020
L	10.400	9.400	0.409	0.370
L1	3.000	2.400	0.118	0.094
L2	6.200	5.300	0.244	0.209
L3	1.200	0.600	0.047	0.024
$\theta$	9°	3°	9°	3°